

On page 4, after line 8, please add the following paragraph as follows:

Fig. 5 is a schematic cross-sectional view illustrating a light-emitting diode according to a second embodiment of the present invention.

On page 7, lines 8-11, please amend the following paragraph as follows:

[In other embodiments of the present invention, the places of the n-type semiconductor layer and the p-type semiconductor layer can be exchanged. In such embodiments, the electrode over the n-type semiconductor layer will be of high reflectivity of light and provides current spreading effect.]
In a second embodiment of the present invention as illustrated in FIG.5, the places of the n-type semiconductor layer 32 and the p-type semiconductor layer 33 can be exchanged. In such an embodiment, the electrode 36 over the n-type semiconductor layer 32 may be of high reflectivity of light and may provide current spreading effect. Said electrode can be of a multi-layer structure comprising a light-transmitting conductive layer and a layer of [aluminium] aluminum (Al) or silver (Ag). In embodiments of the present invention, said electrode can be of a multi-layer structure of Ti/Al, Ti/Ag, ITO/Al or ITO/Ag.

In the Drawings

Please add FIGURE 5 (enclosed herewith). Support for FIGURE 5 is found in the originally filed application on page 3, lines 19-23, and on page 7, lines 8-11. No new matter has been introduced.